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501.36931CX1
Expedited Procedure
Group No. 2813
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: IWASAKI, et al

Serial No.: 09/985,904

Filed: November 6, 2001

For: SEMICONDUCTOR DEVICE HAVING LAYERED
INTERCONNECT STRUCTURE WITH A COPPER OR PLATINUM
CONDUCTING FILM AND A NEIGHBORING FILM (As Amended)

Group Art Unit: 2813

Examiner: Stephen W. Smoot

AMENDMENT AFTER FINAL REJECTION ✓

Assistant Commissioner for Patents
Washington, D.C. 20231
Attn: Box AF

May 12, 2003

Sir:

In response to the Office Action mailed February 11, 2003, please amend the
above-identified application as follows:

IN THE CLAIMS:

Please amend the claims presently in the application as follows:

1. (Twice Amended) A semiconductor device having a layered interconnection

structure including a copper film overlying a surface of a semiconductor substrate,
wherein the layered interconnection structure includes the copper film and a
neighboring film located adjacent to the copper film, the neighboring film having, as a
primary constituent element thereof, an element selected from a group consisting of

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S.W.S.
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